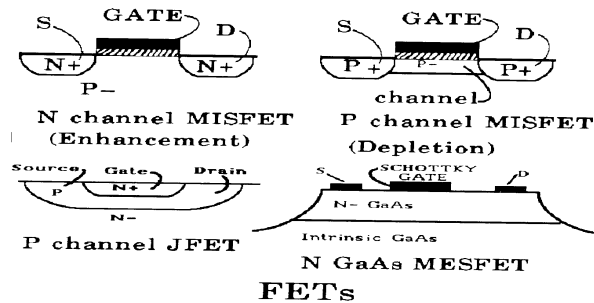


CLASS 438, SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS:

This subclass is indented under the class definition. Process for forming or altering a pair of device active regions (i.e., source or drain) separated by a gate structure intended to permit or block the flow of electrical current therebetween.

(1) Note. To be proper hereunder, the claim must include a positive recitation of (a) formation of semiconductive active regions or (b) altering the electrical properties of active semiconductive regions of the substrate.



SEE OR SEARCH THIS CLASS, SUBCLASS:

49, for a process of making a chemically sensitive field effect transistor (i.e., CHEMFET.)

167 . Having Schottky gate (e.g., MESFET, HEMT, etc.):

This subclass is indented under subclass 142. Process for making a field effect transistor which possesses a gate which forms a metal-semiconductor rectifying junction with the underlying semiconductive active channel region.

180 .. Self-aligned:

This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor wherein a previously formed device feature is utilized to make device regions in the desired registration to the previously formed feature.

(1) Note. A self-aligned gate is one which is aligned between the source and drain via a masking process which uses the gate material itself to achieve the registration of the related device regions.

181 ... Doping of semiconductive region:

This subclass is indented under subclass 180. Process wherein a semiconductive region of the substrate is changed in electrical properties by introduction of an electrically active impurity.

183 Dummy gate:

This subclass is indented under subclass 181. Process wherein a temporary gate is formed or utilized at any stage in the process and is intended to be removed or have no function in the final device.